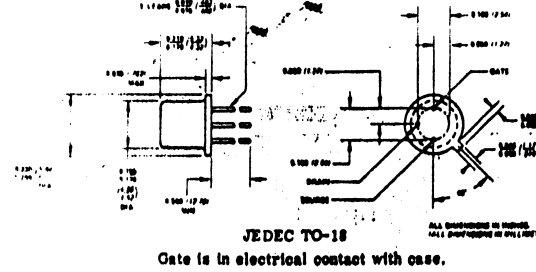


N-CHANNEL SILICON JUNCTION
FIELD-EFFECT TRANSISTORS

FOR SMALL-SIGNAL LOW-NOISE APPLICATIONS



PRODUCT CONDITIONING

Units receive the following treatment before final electrical tests:

- High Temp Storage: 24 Hours at 150°C
- 25,000g Acceleration/Impact in the Y₁ Plane
- Thermal Shock: +100 to 0°C for 5 Cycles
- Helium and/or Gross Leak Tests for Hermeticity

*ABSOLUTE MAXIMUM RATINGS (25°C)

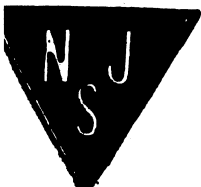
- Gate-Drain or Gate-Source Voltage (Note 1) -5
- Gate Current 10
- Total Device Dissipation at (or below) 25°C Free-Air Temperature (Note 2) 300
- Storage Temperature Range -65 to +20

*ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

| Characteristic | Test Conditions | 2N3458 | | 2N3459 | | 2N3460 | | Units |
|----------------------|--|--------|------------|--------|-----------|--------|-----------|-----------|
| | | Min | Max | Min | Max | Min | Max | |
| I _{GSS} | Gate Reverse Current V _{GS} = -30 V, V _{DS} = 0 | | -0.25 | | -0.25 | | -0.25 | nA |
| | | | -0.5 | | -0.5 | | -0.5 | μA |
| BV _{DGR} | Drain-Gate Breakdown Voltage I _D = 1 μA, I _G = 0 | -50 | | -50 | | -50 | | V |
| I _{D(GOFF)} | Drain Cutoff Current V _{DS} = 20 V, V _{GS} = (-1) | | 1 (-8) | | 1 (-4) | | 1 (-2) | nA (V) |
| V _P | Gate-Source Pinch-Off Voltage V _{DS} = 20 V, I _D = 1 μA | | -7.8 | | -3.4 | | -1.8 | V |
| I _{DSS} | Drain Current at Zero Gate Voltage V _{DS} = 20 V, V _{GS} = 0 | 3.0 | 15.0 | 0.8 | 4.0 | 0.2 | 1.0 | mA |
| g _{fs} | Common-Source Forward Transconductance V _{DS} = 20 V, V _{GS} = 0, f = 1 kHz | 2500 | 10,000 | 1500 | 6000 | 800 | 4500 | μmhos |
| g _{oss} | Common-Source Output Conductance (Input Shorted) V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz | | 35 | | 20 | | 5 | μmhos |
| C _{oss} | Common-Source Output Capacitance (Input Shorted) V _{DS} = 30 V, V _{GS} = 0, f = 1 MHz | | 5 | | 5 | | 5 | pF |
| C _{iss} | Common-Source Input Capacitance (Output Shorted) V _{GS} = 0, V _{DS} = (-1), f = 1 MHz | | 18 (10) | | 18 (8) | | 18 (4) | pF (V) |
| NF | Noise Figure V _{DS} = 10 V, V _{GS} = 0, f = 20 Hz, R _{gen} = 1 meg, BW = 4 Hz | | 6 | | 4 | | 4 | dB |

NOTES:

- Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
- Derate linearly to 200°C free-air temperature at rate of 1.7 mW/°C.
- JEDEC registered data.



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.